



8092US-2S DIV

#15/Amend
1-23-03
C Moore

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF: :
HIRONOBU KON ET AL : GROUP ART UNIT: 2814
SERIAL NO. 09/684,904 :
RCE FILED: HEREWITH : EXAMINER: FARAHANI, D.
FOR: VOLTAGE-DRIVEN POWER :
SEMICONDUCTOR DEVICE :

AMENDMENT UNDER 37 CFR §1.114 AND §1.111

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the outstanding Office Action mailed September 19, 2002, please
amend the above-identified application as follows:

IN THE CLAIMS

Please amend Claims 23, 25, 27, 29, and 31 as shown in the attached marked-up copy
to read as follows:

23. (Twice Amended) An injection enhanced gate transistor (IEGT) made of a
semiconductor chip, comprising:
a collector formed on one side of said semiconductor chip;
a main emitter formed on an opposing side of the semiconductor chip that opposes
said one side of the semiconductor chip;

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